

Is Now Part of



ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at www.onsemi.com

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild guestions@onsemi.com.

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any EDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officer

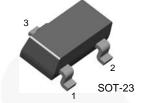


October 2014

KST2222A NPN Epitaxial Silicon Transistor

Features

· General-Purpose Transistor



1. Base 2. Emitter 3. Collector

Ordering Information

Part Number	Marking	Package	Packing Method
KST2222AMTF	1P	SOT-23 3L	Tape and Reel

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_A = 25^{\circ}\text{C}$ unless otherwise noted.

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	75	V
V _{CEO}	Collector-Emitter Voltage 40		
V _{EBO}	Emitter-Base Voltage	6	V
I _C	Collector Current	600	
T _{STG}	Storage Temperature Range	-55 to +150	°C

Thermal Characteristics(1)

Values are at $T_A = 25$ °C unless otherwise noted.

Symbol	Parameter	Value	Unit
P _D	Power Dissipation	350	mW
	Derate Above 25°C	2.8	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	357	°C/W

Note:

1. PCB size: FR-4, 76 mm x 114 mm x 1.57 mm (3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.

Electrical Characteristics

Values are at $T_A = 25$ °C unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Max.	Unit
BV _{CBO}	Collector-Base Breakdown Voltage	$I_C = 10 \mu A, I_E = 0$	75		V
BV _{CEO}	Collector-Emitter Breakdown Voltage	$I_C = 10 \text{ mA}, I_B = 0$	40		V
BV _{EBO}	Emitter-Base Breakdown Voltage	$I_E = 10 \mu A, I_C = 0$	6		V
I _{CBO}	Collector Cut-Off Current	$V_{CB} = 60 \text{ V}, I_{E} = 0$		0.01	μΑ
	DC Current Gain ⁽²⁾	$V_{CE} = 10 \text{ V}, I_{C} = 0.1 \text{ mA}$	35		
h _{FE}		$V_{CE} = 10 \text{ V}, I_{C} = 1 \text{ mA}$	50		
		$V_{CE} = 10 \text{ V}, I_{C} = 10 \text{ mA}$	75		
		$V_{CE} = 10 \text{ V}, I_{C} = 150 \text{ mA}$	100	300	
		$V_{CE} = 10 \text{ V}, I_{C} = 500 \text{ mA}$	40		
\/ (aat)	Callactor Emitter Seturation Valtage (2)	$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$		0.3	V
V _{CE} (sat)	Collector-Emitter Saturation Voltage ⁽²⁾	$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		1.0	
) /	Page Emitter Seturation Valtage(2)	$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$	0.6	1.2	V
V _{BE} (sat)	Base-Emitter Saturation Voltage ⁽²⁾	$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		2.0	
f _T	Current Gain Bandwidth Product	I _C = 20 mA, V _{CE} = 20 V, f = 100 MHz	300		MHz
C _{ob}	Output Capacitance	V _{CB} = 10 V, I _E = 0, f = 1 MHz		8	pF
NF	Noise Figure	I_C = 100 μA, V_{CE} = 10 V, R_S = 1 kΩ, f = 1 MHz		4	dB
t _{ON}	Turn-On Time	$V_{CC} = 30 \text{ V}, I_{C} = 150 \text{ mA},$ $V_{BE} = 0.5 \text{ V}, I_{B1} = 15 \text{ mA}$		35	ns
t _{OFF}	Turn-Off Time	$V_{CC} = 30 \text{ V}, I_{C} = 150 \text{ mA},$ $I_{B1} = I_{B2} = 15 \text{ mA}$		285	ns

Note:

2. Pulse test: Pulse width \leq 300 μ s, duty cycle \leq 2%

Typical Performance Characteristics

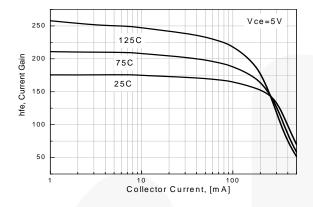


Figure 1. DC Current Gain

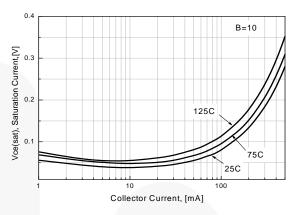


Figure 2. Collector-Emitter Saturation Voltage

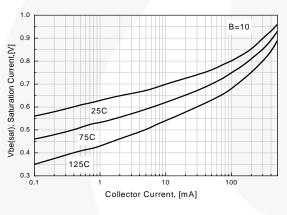


Figure 3. Base-Emitter Saturation Voltage

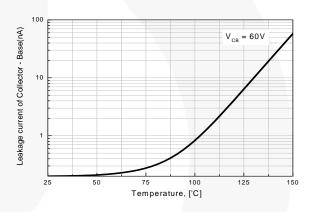


Figure 4. Collector-Base Leakage Current

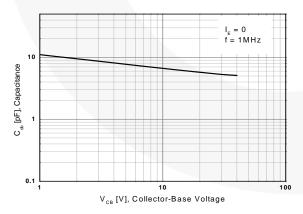


Figure 5. Output Capacitance

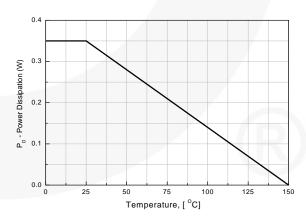


Figure 6. Power Dissipation vs. Ambient Temperature



ON Semiconductor and in are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdt/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and exp

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81–3–5817–1050

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bipolar Transistors - BJT category:

Click to view products by ON Semiconductor manufacturer:

Other Similar products are found below:

619691C MCH4017-TL-H BC546/116 BC557/116 BSW67A NTE158 NTE187A NTE195A NTE2302 NTE2330 NTE63 C4460

2SA1419T-TD-H 2SA1721-O(TE85L,F) 2SA2126-E 2SB1204S-TL-E 2SC5488A-TL-H 2SD2150T100R SP000011176 FMMTA92QTA

2N2369ADCSM 2SC2412KT146S 2SC5490A-TL-H 2SD1816S-TL-E 2SD1816T-TL-E CMXT2207 TR CPH6501-TL-E MCH4021-TL-E

US6T6TR 732314D CMXT3906 TR CPH3121-TL-E CPH6021-TL-H 873787E IMZ2AT108 UMX21NTR EMT2T2R MCH6102-TL-E

FP204-TL-E NJL0302DG 2N3583 2SA1434-TB-E 2SC3143-4-TB-E 2SD1621S-TD-E NTE103 30A02MH-TL-E NSV40301MZ4T1G

NTE101 NTE13 NTE15